

Silicon NPN Power Transistors

2SC1619

DESCRIPTION

- With TO-3 package
- High current capacity
- Wide safe operating area

APPLICATIONS

- For audio frequency output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

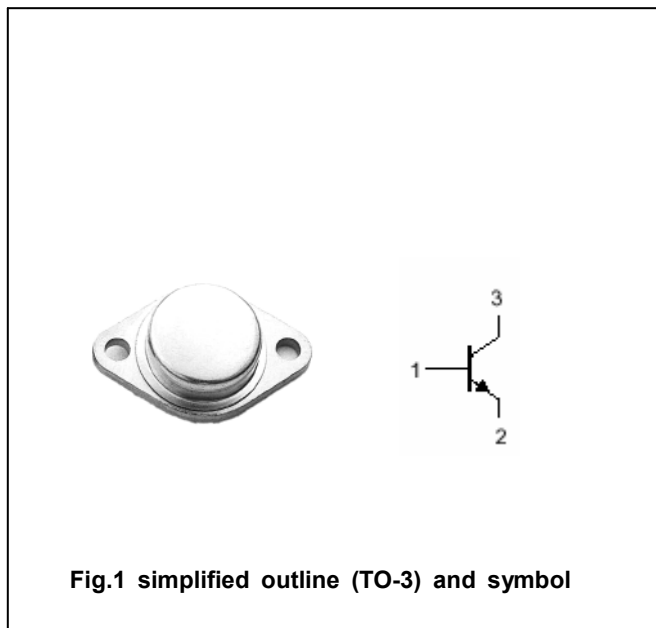


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		6	A
I_{CM}	Collector current-peak		10	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

Silicon NPN Power Transistors

2SC1619

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =100mA; I _B =0	80			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4 A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =0.4 A			2.5	V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =4V	20		180	
f _T	Transition frequency	I _C =0.5A ; V _{CE} =12V		10		MHz

Silicon NPN Power Transistors

2SC1619

PACKAGE OUTLINE

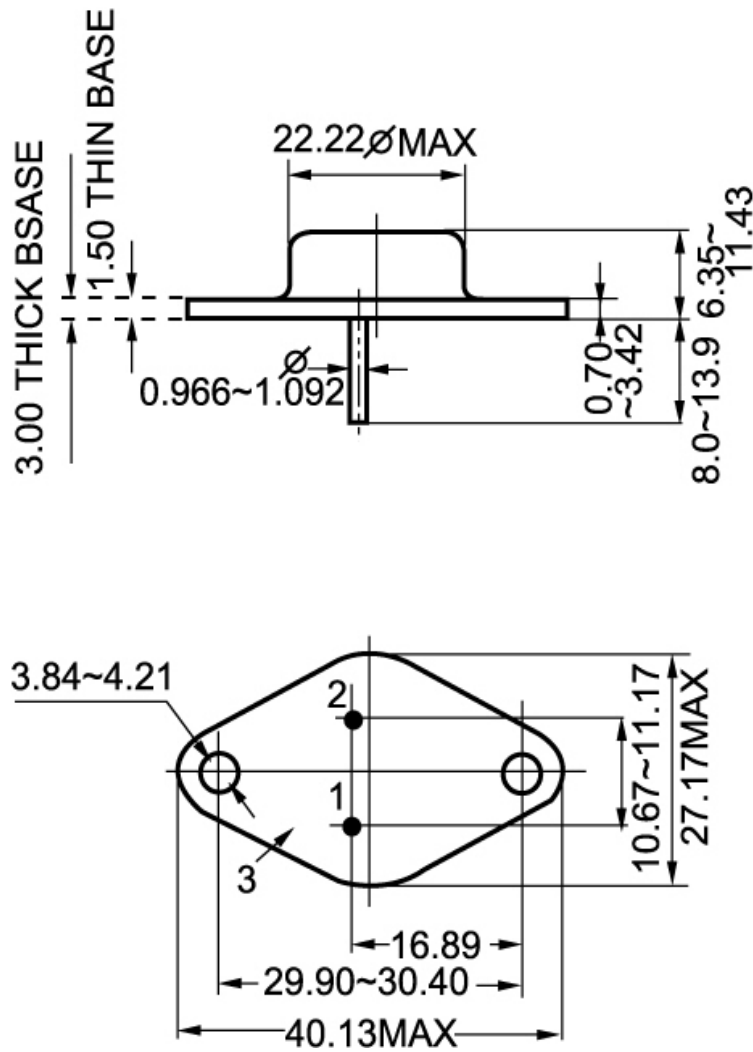


Fig.2 Outline dimensions